TC74HCT563AP/AF
TC74HCT573AP/AF/AFW

Octal D-Type Latch with 3-State Output
TC74HCT563A Inverting
TC74HCT573A Non-Inverting

The TC74HCT563A and TC74HCT573A are high speed CMOS OCTAL LATCH with 3-STATE OUTPUT fabricated with silicon gate C^2MOS technology.

They achieve the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

Their inputs are compatible with TTL, NMOS and CMOS output voltage levels.

These 8-bit D-type latches are controlled by a latch enable input (LE) and a output enable input ($\overline{OE}$).

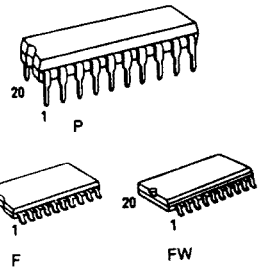
When the $\overline{OE}$ input is high, the eight outputs are in a high impedance state.

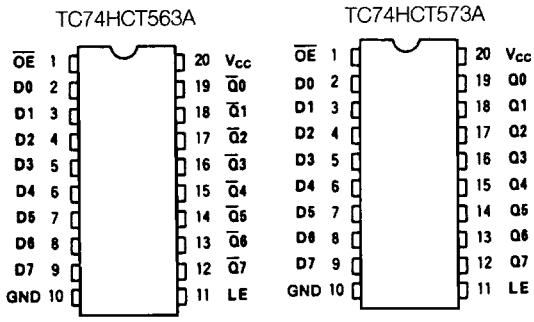
The TC74HCT563A has inverting outputs, and TC74HCT573A has non-inverting outputs.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

Features

- High Speed: t_{pd} = 18ns(Typ.) at V_{CC} = 5V
- Low Power Dissipation: I_{CC} = 4μA(Max.) at Ta = 25°C
- Compatible with TTL outputs: V_{IH} = 2V(Min.)
  V_{IL} = 0.8V(Max.)
- Output Drive Capability: 15 LSTTL Loads
- Symmetrical Output Impedance: $|I_{OH}| = I_{OL}$ = 6mA(Min.)
- Balanced Propagation Delays: $t_{pLH} = t_{pHL}$
- Pin and Function Compatible with 74LS563/573



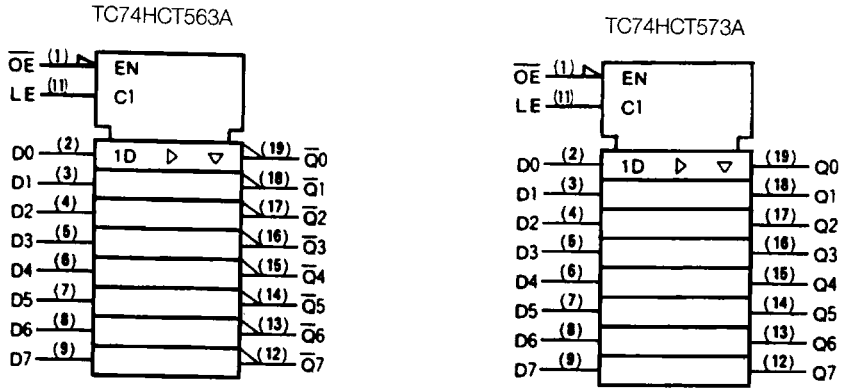


Pin Assignment

Truth Table

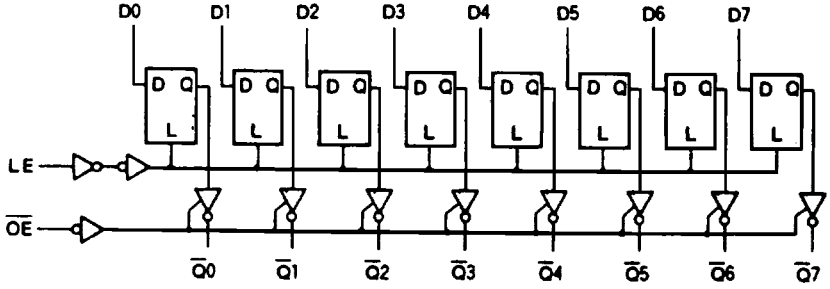
Inputs			Outputs	
$\overline{OE}$	LE	D	Q(HCT573A)	$\overline{Q}$(HCT563A)
H	X	X	Z	Z
L	L	X	Qn	$\overline{Qn}$
L	H	L	L	H
L	H	H	H	L

X: Don't Care
Z: High Impedance
Q_n($\overline{Q}_n$): Q($\overline{Q}$) outputs are latched at the time when the le input is taken to a low logic level.

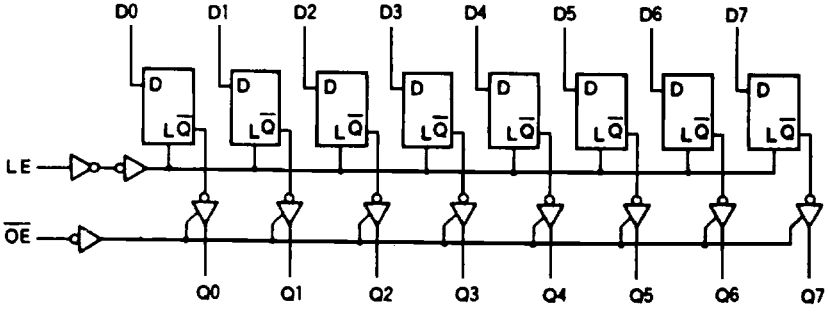


IEC Logic Symbol

TC74HCT563A



TC74HCT573A



Logic Diagram

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply Voltage Range	V_{CC}	-0.5 ~ 7	V
DC Input Voltage	V_{IN}	-0.5 ~ V_{CC} + 0.5	V
DC Output Voltage	V_{OUT}	-0.5 ~ V_{CC} + 0.5	V
Input Diode Current	I_{IK}	±20	mA
Output Diode Current	I_{OK}	±20	mA
DC Output Current	I_{OUT}	±35	mA
DC V_{CC}/Ground Current	I_{CC}	±75	mA
Power Dissipation	P_D	500(DIP)*/180(SOIC)	mW
Storage Temperature	T_{stg}	-65 ~ 150	°C
Lead Temperature 10sec	T_L	300	°C

*500mW in the range of Ta = -40°C ~ 65°C. From Ta = 65°C to 85°C a derating factor of -10mW/°C shall be applied until 300mW.

Recommended Operating Conditions

Parameter	Symbol	Value	Unit
Supply Voltage	V_{CC}	4.5 ~ 5.5	V
Input Voltage	V_{IN}	0 ~ V_{CC}	V
Output Voltage	V_{OUT}	0 ~ V_{CC}	V
Operating Temperature	T_{opr}	-40 ~ 85	°C
Input Rise and Fall Time	t_r, t_f	0 ~ 500	ns

DC Electrical Characteristics

Parameter	Symbol	Test Condition		V_{CC}	Ta = 25°C Min.	Ta = 25°C Typ.	Ta = 25°C Max.	Ta = -40 ~ 85°C Min.	Ta = -40 ~ 85°C Max.	Unit
High-Level Input Voltage	V_{IH}	–		4.5 5.5	2.0	–	–	2.0	–	V
Low-Level Input Voltage	V_{IL}	–		4.5 5.5	–	–	0.8	–	0.8	V
High-Level Output Voltage	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = -20μA	4.5	4.4	4.5	–	4.4	–	V
			I_{OH} = -6 mA	4.5	4.18	4.31	-	4.13	–	
Low-Level Output Voltage	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 20μA	4.5	–	0.0	0.1	–	0.1	V
			I_{OL} = 6 mA	4.5	–	0.17	0.26	–	0.33	
3-State Output Off-State Current	I_{OZ}	V_{IN} = V_{IH} or V_{IL} V_{OUT} = V_{CC} or GND		5.5	–	–	±0.5	–	±5.0	μA
Input Leakage Current	I_{IN}	V_{IN} = V_{CC} or GND		5.5	–	–	±0.1	-	±1.0	μA
Quiescent Supply Current	I_{CC}	V_{IN} = V_{CC} or GND		5.5	–	–	4.0	–	40.0	
	ΔI_{CC}	Per input: V_{IN} = 0.5V or 2.4V Other input: V_{CC} or GND		5.5	–	–	2.0	–	2.9	mA

Timing Requirements (Input $t_r = t_f = 6ns$)

Parameter	Symbol	Test Condition		Ta = 25°C		Ta = -40 ~ 85°C	Unit
			V_{CC}	Typ.	Limit	Limit	
Minimum Pulse Width (LE)	$t_{W(L)}$ $t_{W(H)}$	–	4.5 5.5	– –	15 14	19 17	ns
Minimum Setup Time (Data)	t_s	–	4.5 5.5	– –	10 9	13 11	
Minimum Hold Time	t_h	–	4.5 5.5	– –	5 5	5 5	

AC Electrical Characteristics ($C_L = 50pF$, Input $t_r = t_f = 6ns$)

Parameter	Symbol	Test Condition			Ta = 25°C			Ta = -40 ~ 85°C		Unit
			CL	V_{CC}	Min.	Typ.	Max.	Min.	Max.	
Output Transition Time	t_{TLH} t_{THL}	–	50	4.5 5.5	– –	7 6	12 11	– –	15 14	ns
Propagation Delay Time (LE-Q, $\overline{Q}$)	t_{pLH} t_{pHL}	–	50	4.5 5.5	– –	19 17	29 26	– –	36 33	
			150	4.5 5.5	– –	24 22	37 34	– –	46 43	
Propagation Delay Time (D-Q, $\overline{Q}$)	t_{pLH} t_{pHL}	–	50	4.5 5.5	– –	17 14	26 23	– –	23 21	
			150	4.5 5.5	– –	22 20	34 31	– –	43 39	
Output Enable Time	t_{pZL} t_{pZH}	$R_L = 1k\Omega$	50	4.5 5.5	– –	18 15	27 24	– –	34 30	
			150	4.5 5.5	– –	23 20	35 32	– –	44 40	
Output Disable Time	t_{pLZ} t_{pHZ}	$R_L = 1k\Omega$	50	4.5 5.5	– –	18 16	24 22	– –	30 28	
Input Capacitance	C_{IN}	–			–	5	10	–	10	pF
Output Capacitance	C_{OUT}	–			–	10	–	–	–	
Power Dissipation Capacitance	C_{PD}(1)	TC74HCT563A			–	37	–	–	–	
		TC74HCT573A			–	38	–	–	–	

Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.
Average operating current can be obtained by the equation:

$$I_{CC(opr)} = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/8\text{(per Latch)}$$

And the total C_{PD} when n pcs. of Latch operate can be gained by the following equation:

C_{PD}(total) = 25 + 12 • n (TC74HC563A)
C_{PD}(total) = 25 + 12 • n (TC74HC573A)